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54 Miniaturized monolithic multi-layer capacitor and apparatus and method for making.

57 A monolithic multi-layer capacitor is disclosed having a central capacitively active area and two electrode joining sections separated from the active area by sloped sections. The dielectric layers are about 1 micron thick in the active area and taper gradually to zero thickness in the sloped sections. Electrode layers in the active area have a thickness in the range from 200 to 500 Angstroms and sufficient thickness throughout the sloped sections for adequate current carrying capacity. Various acrylates are used for the dielectric layers, the number of layers ranging from a few to many thousands.

Apparatus and methods are disclosed for the fabrication of such capacitors on a high speed, production scale basis. Such employ techniques for the flash evaporation of highly reactive monomers of acrylate dielectric materials so as to form a gaseous stream of such materials. The gas stream is controllably directed to a deposition surface for condensation and subsequent curing by a field enhanced gas discharge electron beam source. The control of the dielectric gas stream is accomplished by means of adjacent gas streams of an inert gas directed to areas of the deposition surface where deposition of the electrode material is un-

wanted. Means are disclosed for the atomization of the monomers of the dielectric material in preparation for its flash evaporation.

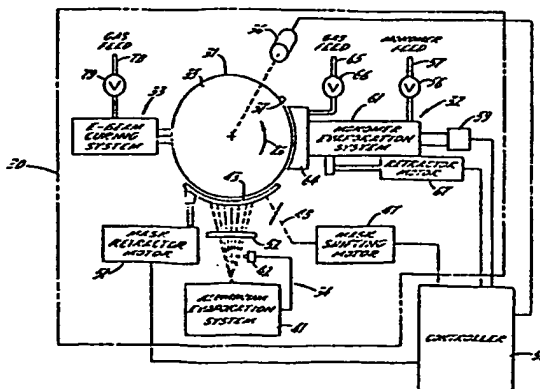


FIG. 2.

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Field of the Invention

5        This invention relates generally to electrical monolithic capacitors and more particularly concerns miniature multi-layered capacitors together with methods and apparatus for making them.

Cross References

10 This application is related to the following co-pending, simultaneously filed, commonly assigned patent applications: Serial No. 562,873, filed December 19, 1983, entitled "Capacitor With Resin Dielectric And Method Of Making"; Serial No. 562,871, filed December 19, 1983,  
15 entitled "Capacitors Containing Polyfunctional Acrylate Polymers As Dielectrics"; Serial No. 562,893, filed December 19, 1983, entitled "1; 2-Alkanediol Diacrylate Monomers And Polymers Thereof Useful As Capacitor Dielectrics"; Serial No. 562,872,  
20 filed December 19, 1983, entitled "Acrylate-Containing Mixed Ester Monomers And Polymers Thereof Useful As Capacitor Dielectrics"; and Serial No. 562,894, filed December 19, 1983, entitled "Polyfunctional Acrylate Monomers For  
25 Polymers Thereof Useful As Capacitor Dielectrics", all of which are hereby incorporated by reference.

Background And Objects Of The Invention

A monolithic capacitor is one in which the layers of electrodes and dielectric are bonded  
30 together in a unitary structure as opposed, for example, to a metallized film capacitor in which self-supporting films are rolled or wound into the capacitor form. A miniaturized capacitor is one of very small dimensions, so as to be suitable for  
35 microcircuitry. Small overall size could denote low

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capacitance of little practical value, except that the thickness of the intervening dielectric layer inversely affects the capacitance between adjacent electrodes, and the number of electrode pairs  
5 directly affects capacitance. Therefore, as a matter of basic capacitor theory, a capacitor having very thin dielectric layers and many pairs of electrodes could have substantial capacitance despite being of miniature size with the active area of the electrodes  
10 being quite small.

Modern microcircuitry not only is well suited for miniature capacitors, but a further requirement of such capacitor applications is an ability to withstand high temperatures. In an electronic  
15 circuit, a capacitor could be subject to sustained temperatures of up to 230°C. Even more demanding, circuit production techniques such as wave soldering could subject capacitors to temperatures beyond the melting point of solder, about 280°C., for as long as  
20 10 to 30 seconds.

It is an object of the invention to provide an improved capacitor concept, including the capacitor architecture itself as well as the methods and apparatus for forming that architecture, that  
25 produces a very small, miniature capacitor which nevertheless has practical levels of capacitance.

A primary object is also to provide a concept of the foregoing kind that can very economically produce capacitors, both in the sense of using limited  
30 amounts of materials as well as permitting high volume, high speed capacitor manufacturing. A related object is to provide such a concept in which the electrical connections or leads can be easily and economically added to individual capacitors, and the  
35 capacitor encapsulated without difficulty.

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Another object is to provide a concept as characterized above that results in a capacitor capable of withstanding substantial temperatures such as the 280°C. encountered during the process of wave soldering. A collateral object is to provide a concept of this kind that could readily be mounted on the bottom or foil side of a circuit board so as to permit compaction of the required physical size of a circuit using such capacitors.

It is also an object to provide a concept of the above character that is not polarity sensitive, i.e., the capacitor is reversible. An accompanying object is to provide such a concept in which the capacitor fails open, in other words, it is self-healing rather than being subject to shorting out in a circuit.

Other objects and advantages of the invention will become apparent upon reading the following detailed description and upon reference to the drawings, in which:

Figure 1 is an enlarged cross section of a capacitor embodying one form of the invention before completion;

Fig. 1a is a perspective of a completed capacitor of the Fig. 1 type;

Fig. 2 is a schematic of an apparatus embodying one form of the invention;

Fig. 3 is a fragmentary perspective of a portion of the apparatus shown in Fig. 2;

Figs. 4a and 4b are cross sections of a portion of the apparatus shown in Fig. 2 illustrating alternate positions and the resulting modes of operation;

Fig. 5 is an enlarged, partially sectioned, diagram of a portion of the apparatus shown in Fig.

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Fig. 6 is an alternate apparatus to that shown in Fig. 5;

Fig. 7 is a fragmentary diagram of a portion of the apparatus shown in Fig. 2;

5 Fig. 8 is a bottom elevation of the apparatus shown in Fig. 7;

Fig. 9 is a perspective of the apparatus shown in Fig. 8;

10 Fig. 10 is a fragmentary perspective of a group of the Fig. 1 capacitors in the form in which they are manufactured;

Fig. 11 is a fragmentary perspective, partially sectioned, of a portion of the apparatus shown in Fig. 2;

15 Fig. 12 is a section taken approximately along the line 12-12 in Fig. 11; and

Fig. 13 is a perspective similar to Fig. 10 but showing an alternative capacitor group manufactured in a similar manner.

20 While the invention will be described in connection with preferred embodiments and procedures, it will be understood that we do not intend to limit the invention to those embodiments or procedures. On the contrary, we intend to cover all alternatives, 25 modifications and equivalents as may be included within the spirit and scope of the invention as defined by the appended claims.

Turning to the drawings, there is shown in Figs. 1 and 1A a capacitor 10 embodying the inventive 30 concept including an encapsulated body 11 with extending connecting wire leads 12. The Fig. 1 cross section, showing a conductive substrate 13 notched at 14 into separate pieces, conductive layers 15, and dielectric coatings 16, illustrate the capacitor 10 35 before the leads 12 are connected to the respective

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pieces of the substrate 13 and the capacitor is encapsulated.

Preferably, the substrate 13 is copper sheet about 1.5-2 mils thick. The conductive layers 15 are  
5 electrode material such as aluminum about 200-500 Angstroms thick, and the dielectric coatings 16, about 1 micron thick in the center region, are cured, i.e., cross linked, radiation curable resin capable of adhering or bonding to the electrode material and  
10 substrate. Useful resins are polyfunctional acrylics, and mixtures thereof, disclosed in the patent applications cross referenced above.

As will be apparent from the dimensions given, even a miniature capacitor of this design which is  
15 less than 1 inch square in outer periphery and a few millimeters thick can embody many alternate electrode and dielectric layers, up to 1000 or more. The result is a capacitor effective at up to 50 volts with a capacitance in the 0.001 to 100 microfarad  
20 range, depending, of course, upon overall size and the number of electrode pairs.

The dielectric coatings 16 space and separate the conductive layers 15 which are, in effect, divided into two offset sets that extend into a  
25 capacitance section or region 17 in which the layers 15 are uniformly interleaved in stacked electrically isolated relation.

Pursuant to the invention, there are terminal portions 18 on the substrate 13 defining electrical  
30 joining sections ending at cut-off lines 19 spaced substantially from the opposite, and separated, edges of the central capacitance region 17. The coatings 16 taper from uniform thickness in the uniform capacitor region 17 to zero thickness adjacent the  
35 terminal portions 18, so that the capacitor has

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sloped portions 21. The spacing of the cut-off lines 19 and the terminal portions 18 from the central capacitance region 17 is sufficient so that the uppermost coating 16 in a given capacitor has a horizontal dimension, horizontal being the plane of the substrate 13, that permits the acceptance of a final conductive layer 15 in the sloped portions 21. That is, assuming the electrode material will be vapor deposited virtually perpendicular to the substrate 13, and that the layers 15 in the sloped portions 21 will be steeper and steeper with respect to the substrate as additional layers are built up, the initial capacitor region-cut-off line spacing must be great enough so that the final electrode layer 15 is not required to be vertical to the substrate. In practice, when working with coatings and layers having the thicknesses indicated, it is desirable to space the terminal portions 18 at least 10 microns from the central capacitance region 17, or else control of the coatings and layers 15, 16 in the sloped portions 21 becomes difficult and the resulting structure build-up unreliable.

It can now be seen that the purpose of the notch 14 is to divide the substrate 13 and thus eliminate electrical connection between the two terminal portions 18.

In carrying out an embodiment of the invention, capacitors like the capacitor 10 are simultaneously formed in large numbers by depositing electrode material and dielectric in strips on the substrate 13 which rapidly moves relative to the depositing systems. The layers 15 and coatings 16 are built up in the number desired by causing successive passes to be made relative to the depositing systems. The result, see Fig. 10, is a series of lanes 25 which

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can be separated along the cut-off lines 19 running in the machine direction 26, a term that will be made evident below, and divided into individual capacitors 10 along cross cut lines 27 spaced in accordance with 5 the nominal capacitance desired. The greater the spacing, the more electrode area each layer 15 will have in the capacitor region 17 of the individual capacitor 10 and the higher will be the resulting capacitance.

10 From the lane configuration, capacitors 10 are thus cut to desired size, the notch 14 is formed, the leads 12 are added, and the device encapsulated.

It can be seen from Fig. 1 that the dielectric coatings 16 can be built up by depositing a coating 15 strip at the same relative position of the substrate 13 after each strip of electrode material has been deposited. To create the interleaved sets of electrode layers 15, in one depositing pass electrode material is deposited in every other terminal portion 20 18 and the adjacent capacitor regions 17, and in the next pass, after an intervening dielectric coating, electrode material is deposited in the terminal portions 18 not previously receiving material and in each adjacent capacitor region 17 (see Figs. 4A and 25 4B).

The inventive capacitor concept, in a preferred form, includes apparatus arranged within and around a chamber 30 (see Fig. 2) which is either a vacuum chamber or a housing divided into vacuum portions. 30 Within a vacuum environment is a carrier 31, a dielectric deposit system 32, a monomer curing system 33, and an electrode material deposit system 34. A substantial vacuum is required down to the order of  $1 \times 10^{-4}$  Torr.



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The carrier 31 is a water cooled drum 35 driven by a motor 36 and whose outer cylindrical surface 37 defines a rapidly moving continuous surface passing through a dielectric forming zone and an electrode forming zone. The regions in which the drum surface 37 and the systems 32, 33 are located constitute the dielectric forming zone, and the region in which the drum surface 37 and the system 34 are located constitute an electrode forming zone. Drum rotation creates the machine direction 26, which is the direction the surface passes through the dielectric forming zone and the electrode forming zone.

Because of the small dimensions involved, the surface 37 should be smooth and true. The sheet of substrate 13 is firmly secured to the drum 35 and, when in place, the outer surface of the substrate defines the surface 37. The drum 35 is cooled to about 70°F. so as to facilitate condensation of the vapor deposits, and the apparatus functions at drum surface speeds of 150 to 600 feet per minute.

The electrode material deposit system 34 includes a conventional electron beam vaporization device 41 such as those used for metallizing film within a vacuum environment. The rate of vaporization is sensed by a conventional quartz monitoring device 42 providing feedback for controlling the rate at which aluminum is vaporized by the device 41.

The pattern in which aluminum vapor is deposited is controlled by a mask, in this case a shadow mask 43, having openings 44 through which the vapor passes. The openings 44 have a main portion 45 wide enough to span the capacitance regions 17 in two adjacent lanes 25 as well as the intermediate terminal portions 18. As the capacitors are built

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up, the sloped portions 21 become greater in surface area and more aluminum is required to lay down an integral layer capable of carrying current. This is achieved by forming the mask openings 44 with an  
5 extension 46 spanning adjacent sloped portions 21 and the intervening terminal portions 18. The amount of electrode material deposited is a function of the time the receiving surface is beneath an open portion of the mask 43, and thus more metal is placed on the  
10 sloped portions 21 than in the capacitance regions 17.

The alternate pattern of metal vapor deposition discussed above in connection with Figs. 4a and 4b is obtained by shifting the mask 43 axially of the drum  
15 35 upon each drum revolution. A mask motor 47 makes the shifting movement through a simple mechanical connection 48. A controller 50 is connected to the drum motor 36 for sensing drum revolution, and the controller 50 supplies the appropriate shifting  
20 signal to the mask shifting motor 47. It is desirable to keep the mask 43 close to the surface onto which the metal vapor is being deposited, and this closeness is maintained by a mask retraction motor 51 which steps the mask away from the surface  
25 37 upon each drum revolution, as signalled by the controller 50, through a distance approximating the thickness of the electrode layer being deposited.

As it is convenient to energize the device 41 and bring it into stable operating condition before  
30 beginning to make capacitors, a removable shutter 52 is interposed between the device 41 and the mask 43 for closing off the passage of vapor until the shutter 52 is withdrawn.

As a feature of the invention, the dielectric  
35 deposit system 32 flash vaporizes the dielectric in

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monomer form, and the smaller gaseous molecules are guided under moderate differential pressure through nozzles 55 onto the capacitor lanes 25. The monomer in liquid form is fed through a line 56 and control valve 57 to the open end of the horn 58 of an ultrasonic atomizer 59. The resulting tiny liquid droplets impinge on the inner walls of a vaporization tube 61 heated by band heaters 62 to an appropriate temperature, approximately 350°C. for the acrylate resins referred to above. The liquid is thus instantaneously vaporized, i.e., flash vaporized, so as to minimize the opportunity for polymerization. The resulting smaller gas molecules tend to follow a straighter path for better control of the deposition.

Pressure in the tube 61, at about 1 Torr, causes a monomer gas stream to flow through the nozzles 55 for deposition and condensation. The nozzles 55 are heated by conduction from the tube 61 to minimize condensation before the gas stream leaves the nozzles.

The deposition is confined, and the tapered edge shape of the coatings 16 obtained, by restricting the monomer gas flow by using guiding deflectors 63 in the nozzles 55, placing the nozzles 55 quite close to the condensing surface of the lanes 25, and providing inert gas edge barrier walls delivered through sets of nozzles 64 on either side of the monomer nozzles 55. Inert gas is supplied to the nozzles 64 through a line 65 and a control valve 66, and the nozzles 64 are fixed relative to the surface 37 with about a 4 mil clearance spacing, sufficient to clear the expected build-up of the terminal portions 18. The monomer gas nozzles 55 are stepped back by a retraction motor 67, signalled by the controller 50,

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upon each revolution of the drum by an amount approximating the thickness of a coating 16.

The thickness of the coating 16 is dependent upon the time of deposit, i.e., the length of the  
5 nozzles 55 relative to the speed of the surface 37, and the rate of monomer flow through the valve 57. By balancing the inert gas flow using the valve 66 against the monomer gas flow, the tapered side of the dielectric coating strips can be controlled.

10 An alternate arrangement for atomizing the liquid monomer is suggested in Fig. 6 wherein the monomer is directed through a capillary tube 68 to a point closely adjacent the horn 58 of the ultrasonic atomizer 59. In this arrangement, a meniscus is  
15 formed between the end of the capillary tube 68 and the end of the horn 58, and the monomer is drawn uniformly through the tube.

The condensed liquid monomer is radiation cured by the second system 33 in the dielectric forming  
20 zone which includes a radiation source, preferably a gas discharge electron beam gun 70. The gun 70 directs a flow of electrons from a housing chamber 71 through an emitter window 72 onto the monomer, thereby curing the material to a polymerized cross  
25 linked form capable of withstanding the high temperatures to which the capacitors 10 might be subject. The cured material is also bonded in place.

The gun 70 includes a rectangular copper cathode 73 supported by a connector 74 in an insulator 75  
30 mounted in a ground shield 76 that is fixed to the housing 71. A tungsten mesh extraction screen 77 is fixed across the window 72. A gas such as argon is fed to the housing chamber 71 through a line 78 and a control valve 79. An electrical potential is imposed  
35 between the cathode 73 and its connector 74, and the

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shield 76, housing 71 and screen 77, with the result, keeping in mind the vacuum environment, that a gaseous plasma is created in the housing, primarily between the cathode 73 and the screen 77. The cathode is preferably formed with grooves 81 on its face so that electrons are expelled in a non-linear beam to substantially fill the housing chamber 71. Because of the plasma created, other electrons are stripped from the ionized gas molecules in different portions of the chamber, a so-called field enhanced effect, with the result that electrons at widely varying energy levels are emitted from the window 72. The wide range of energy levels of the emitted electrons is believed to cause the observed effect that the monomer is cured with little surface charging, and avoiding surface charging on the coatings 16 minimizes the possibility of arcing to the electrode layers. It can also be seen that the gun 70 produces a wide beam of electrons so that a number of capacitor lanes can be simultaneously treated.

The overall operation of the apparatus can now be readily understood. Electrode layers are deposited, coated with dielectric and the dielectric cured, before the surface on which the electrode layers are deposited passes again for successive electrode layers and dielectric coatings. Desired thicknesses of the electrode layers and dielectric coatings are determined by matching the rate of vapor deposition with the surface speed of the drum 35.

It will be apparent that the capacitors 10 are truly miniature capacitors having, nevertheless, useful levels of capacitance. Those familiar with the art will understand that the apparatus and methods disclosed economically produce the capacitors

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10 in the sense that high speed production is possible of large numbers of capacitors simultaneously, as well as in the sense that each individual capacitor uses little raw material.

- 5 Despite the small size of each capacitor, there is, in the design of that capacitor, a usable workable area for securing wire leads so as to complete the assembly. Since the capacitor is made up solely of metal and cured temperature resisting resin, they are
- 10 capable of withstanding substantial temperatures including those temperatures for a limited time resulting from wave soldering assembly techniques.

As a result of the very small dimensions involved in the thicknesses of the electrode layers

15 and dielectric coatings, the capacitor 10 has the property of being self-healing. That is, should a defect exist in a dielectric coating permitting a small amount of metal to electrically connect electrode layers in the opposite sets, the

20 application of current could be expected to burn or melt the very small cross section of connecting metal so as to open the defect. As a result, it is highly unlikely that the capacitor will fail by shorting out.

- 25 The apparatus and methods described above can also be advantageously employed to form capacitors in a full width configuration as opposed to the lane configuration of Fig. 10. As shown in Fig. 13, where elements similar to those already described have been
- 30 given the corresponding reference numeral with the distinguishing suffix a added, capacitors 10a can be formed on a substrate 13a having both the conductive layers 15a and the dielectric coatings 16a of uniform thickness. Separating individual capacitors 10a
- 35 along cut-off lines 19a and cross cut lines 27a

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exposes the edges of the conductive layers 15a and therefore some form of edge termination is required to electrically connect the interleaved layers 15a at the opposite ends of the capacitor.

5       It will be appreciated that this form of capacitor 10a can be formed by eliminating the inert gas nozzles 64 and uniformly depositing the monomer through the system 32. Because the conductive layers 15a are not sloped, there is also no need for the  
10 extension 46 in the shadow mask 43 of the system 34. Otherwise, the capacitors 10a can be made in full width configuration consistent with the width of the systems 32, 33 and 34.

It will be understood that the foregoing  
15 description is only of certain preferred embodiments, and the invention is to be determined by giving the following claims their proper scope and interpretation.

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CLAIMS

1. A high speed apparatus for forming capacitors comprising, in combination, a housing having vacuum portions, a carrier in said housing defining a rapidly moving surface movable  
5 repetitively through said portions, a depositing device in a vacuum portion for depositing conductive layers on said surface, a dielectric depositing device in a vacuum portion for depositing coatings of dielectric on said conductive layers, and means for  
10 controlling each of said devices so that a conductive layer is deposited, and coated with dielectric, before the repetitive surface passes said devices again for successive layers and coatings.

2. A high speed apparatus for forming  
15 capacitors comprising, in combination, a vacuum chamber, a carrier in said chamber defining a rapidly moving continuous surface, a metal depositing device in said chamber for depositing layers of metal on said surface, a dielectric depositing device in said  
20 chamber for depositing coatings of curable dielectric on said metal layers, means in said chamber positioned for curing successive coatings of dielectric as they are deposited, and means for controlling each of said devices so that metal is  
25 deposited, coated with dielectric, and the dielectric is cured before the continuous surface passes said devices again for successive layers, coatings and curings.

3. The combination of claim 2 in which said  
30 carrier is a drum, said metal depositing device evaporates electrode metal, said dielectric depositing device evaporates a curable monomer, and said means for curing includes an electron beam gun.



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4. The combination of claim 3 in which said dielectric depositing device acts to flash vaporize the dielectric, and said beam gun is a gas discharge electron beam gun.

5        5. Apparatus for continuously producing under vacuum a monolithic multi-layer capacitor on a substrate surface comprising, in combination, means for forming a layer of electrode material on a surface within a predefined electrode forming zone,  
10 means for forming a coating of dielectric material on a surface within a predefined dielectric forming zone with said dielectric being bondable with the electrode material, and means for repeatedly passing a substrate surface carrying said layers and coatings  
15 through the two zones in the above sequence so that two different portions of the surface are simultaneously within their respective zones so as to produce alternate layers and coatings of electrode and dielectric on the substrate surface.

20        6. The combination of claim 5 including means for controlling the rates of forming the electrode layers and the dielectric coatings so as to predetermine the thickness of the alternate layers and coatings of electrode and dielectric.

25        7. The combination of claim 5 in which said means for forming a coating of dielectric material includes a first nozzle closely overlying the substrate surface at said dielectric forming zone, and a pair of second nozzles adjacent either side of  
30 said first nozzle for creating an inert gas wall on either side of the dielectric forming zone.

8. The combination of claim 7 including means for stepping said first nozzle away from said substrate surface after each repeated pass so as to maintain the first nozzle close but not in contact  
5 with said coatings.

9. The combination of claim 5 in which said means for forming a layer of electrode material includes means for evaporating metal electrode material and a mask for confining the evaporated metal electrode material to the electrode forming  
10 zone.

10. The combination of claim 9 including means for stepping said mask away from said substrate surface after each repeated pass so as to maintain said mask at substantially the same distance from  
15 said coatings.

11. Apparatus for producing a capacitor under vacuum on a substrate surface comprising, in combination, means for forming a layer of electrode material of given thickness on a surface within a  
20 predefined electrode forming zone, means for forming a coating of curable dielectric material of given thickness on a surface within a predefined dielectric forming zone, a radiation source for curing the dielectric coating within the dielectric forming  
25 zone, means for moving a substrate alternately into the electrode forming zone and the dielectric forming zone, and means for controlling the electrode layer forming means, the dielectric coating forming means, the radiation source and the moving means so as to  
30 produce alternate layers and coatings of electrode and cured dielectric materials of predetermined thicknesses.

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12. The combination of claim 11 in which said radiation source is a gas discharge electron beam gun.

13. The combination of claim 11 in which said  
5 means for forming a coating of dielectric material includes means for generating a gas stream of a curable dielectric material and means for directing and condensing the gas stream so as to form the coating of the dielectric material within preselected  
10 limits on the surface within the predefined dielectric forming zone.

14. The combination of claim 13 in which said means for generating a gas stream does so by flash vaporization, and said means for directing the gas  
15 stream includes a heated nozzle to avoid having dielectric material stick to the nozzle.

15. The method of making a capacitor comprising the steps of depositing successive conductive layers with the layers being offset so as to define a  
20 central capacitance region of stacked electrically isolated extending layers, depositing on each of said layers a coating of dielectric so that the layers in the capacitance region are substantially spaced and separated by a coating of dielectric, said coating  
25 deposition being controlled so as to slope toward cut-off lines spaced substantially from two separated portions of the central capacitor region, said layer deposition extending beyond said cut-off lines so that successive layers fuse into spaced-apart  
30 terminal portions, and said cut-off line spacing being sufficient to cause the uppermost dielectric coating of a multi-layer capacitor to have a horizontal dimension from the capacitor region to the terminal portion to accept a final layer deposition.

16. The method of claim 15 in which said layers and said coatings are deposited successively in long strips with the edges of the strips being defined by said terminal portions, and including the step of  
5 cutting said strips into discreet capacitors.

17. The method of claim 16 including the step of connecting wire leads to the opposite terminal portions of the discreet capacitors.

18. In the method of depositing successive  
10 layers of conductors separated by dielectric to form a capacitor, controlling the depositing of dielectric by the steps of directing vaporized dielectric at a uniform rate to a center region to form a uniform coating dependent on time, defining edge barriers for  
15 said vaporized dielectric spaced from said center region so that dielectric is not deposited past said barriers, and restricting vaporized dielectric flow from said center region to said edge barriers so as to form tapered surfaces from said center region to  
20 said edges.

19. The method of claim 18 in which said edge barriers are defined by flowing walls of inert gas, and said step of restricting vaporized dielectric flow includes balancing the flow rates of said  
25 vaporized dielectric and said inert gas.

20. The process of continuously producing under vacuum a monolithic multi-layer capacitor on a substrate comprising the steps of forming a layer of electrode material on one part of a substrate within  
30 a predefined electrode forming zone, simultaneously forming a coating of dielectric material on another part of the substrate within a predefined dielectric forming zone with said dielectric material being bondable with the electrode material, and repeatedly  
35 passing the substrate through the two zones in

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sequence so as to cyclically change the parts thereof that are within each zone so as to produce alternate layers and coatings of electrode and dielectric on the substrate.

5        21. The process of claim 20 including the step of controlling the rates of forming the electrode layers and the dielectric coatings so as to predetermine the thickness of the alternate layers and coatings of electrode and dielectric.

10        22. The process of producing a capacitor under vacuum on a substrate surface comprising the steps of (a) forming a layer of electrode material of given thickness on a substrate, (b) forming a coating of radiation curable dielectric material of given  
15 thickness within preselected limits on the electrode layer, (c) curing the dielectric coating by means of a radiation source, (d) forming another layer of electrode material of given thickness over the cured dielectric coating, and (e) repeating steps (b), (c)  
20 and (d) a selected number of times so as to produce alternate layers and coatings of electrode and cured dielectric materials of predetermined thicknesses on the substrate.

23. The combination of claim 22 in which said  
25 radiation source is a gas discharge electron beam gun.

24. The process of claim 23 in which the step of forming a coating of dielectric material includes forming a gas stream of a curable dielectric material  
30 and directing and condensing the gas stream so as to form the coating of the dielectric material within the preselected limits.

25. A capacitor comprising, in combination, conductive layers with the layers being offset so as  
35 to define a central capacitance region of stacked

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electrically isolated extending layers, coatings of dielectric on said conductive layers so that the layers in the capacitance region are substantially spaced and separated by a coating of dielectric, said  
5 coatings sloping toward lines spaced substantially from two separated portions of the central capacitor region, said layers extending beyond said lines with successive layers fused into spaced-apart terminal portions, and said line spacing being sufficient to  
10 cause the uppermost dielectric coating of a multi-layer capacitor to having a horizontal dimension from the capacitor region to the terminal portion supporting a final conductive layer.

26. A monolithic multi-layer capacitor having a  
15 capacitively active section, and two electrode joining sections, each separated from the active section by a sloping section, said capacitor comprising first and second sets of electrode layers interleaved with one another, each layer of each set  
20 having an active area extending through and contributing to the capacitively active section of the capacitor in a stacked and spaced apart relationship with the active areas of all the other layers and each layer having an electrode joining  
25 margin in a stacked electrically contacting relationship with the margins of the other layers in its set so as to form an electrode joining section of the capacitor, and each layer having a sloped portion running between its active area and its margin  
30 contributing to a sloped section of the capacitor, and a dielectric coating in adherent contact with and between each adjacent electrode layer pair, said dielectric coating being of substantially uniform

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thickness in the capacitively active section and tapering to zero thickness through the sloping section.

27. The capacitor of claim 26 in which said  
5 active section is spaced from each of said joining sections by more than 10 microns.

28. The product produced by the process of claims 15, 20 or 22.

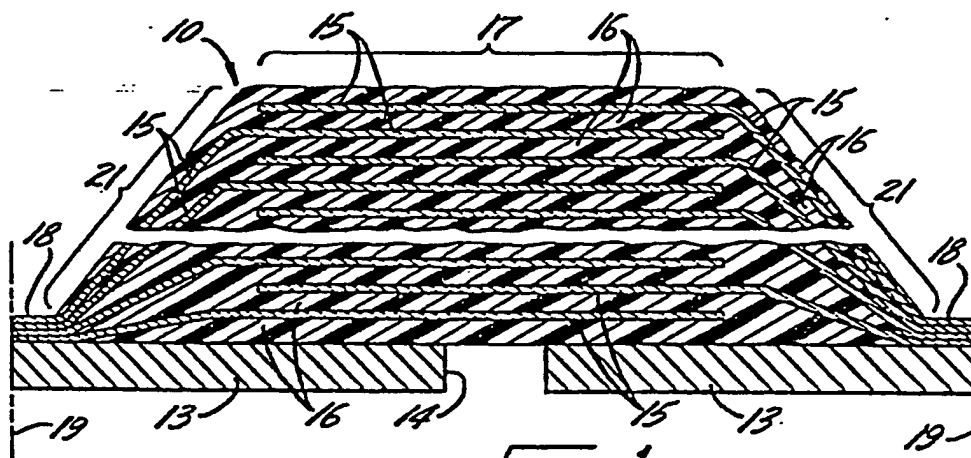


FIG. 1.

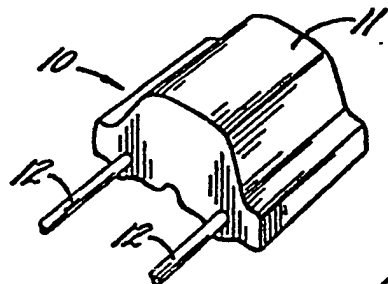


FIG. 1a.

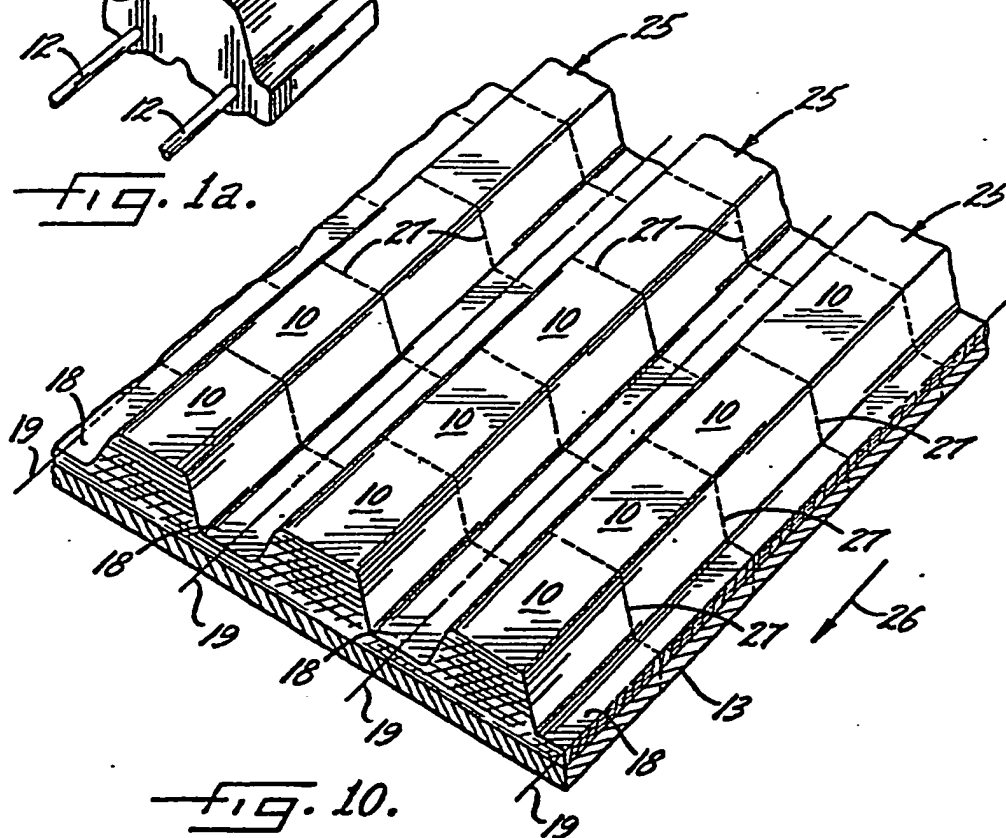
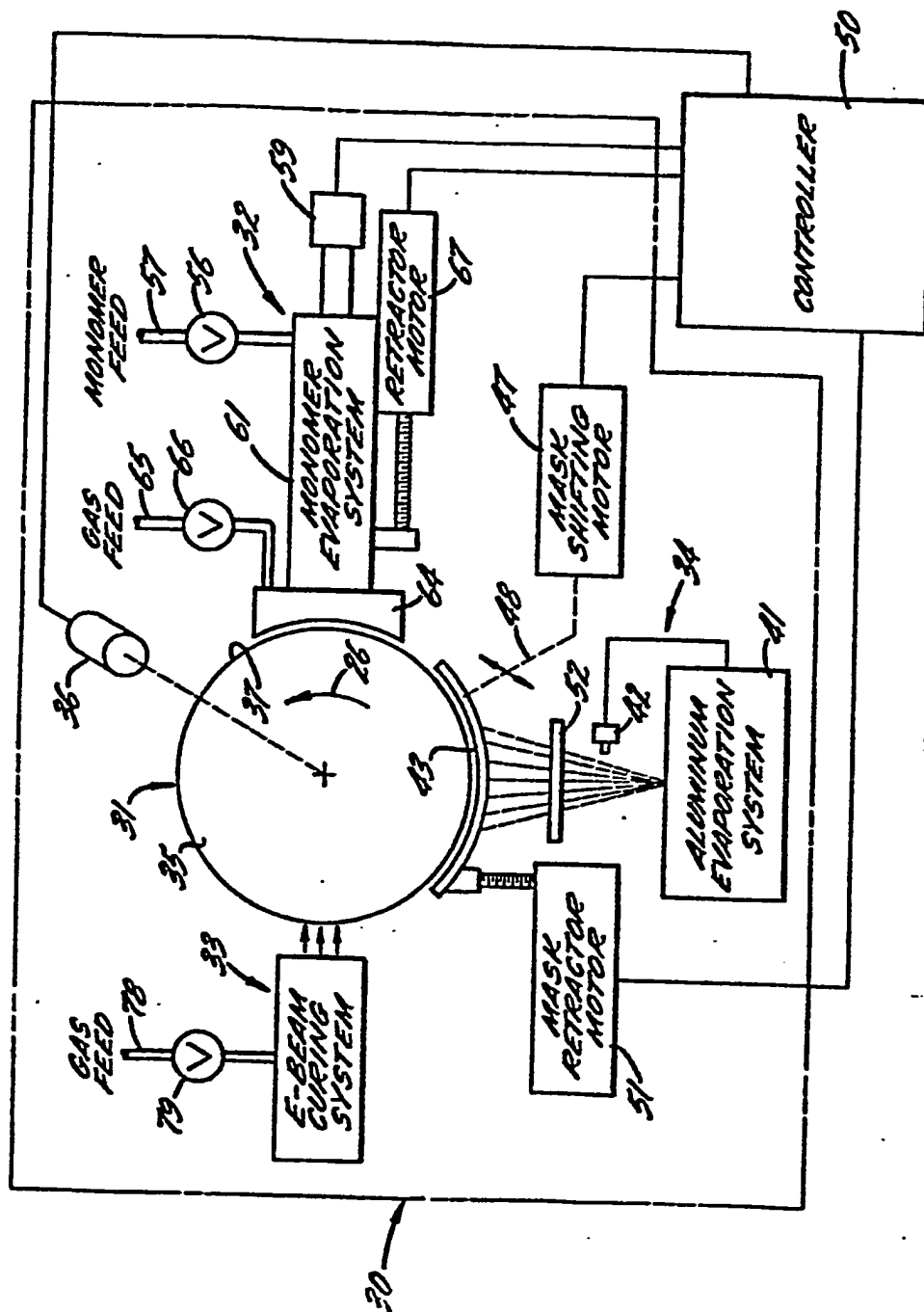
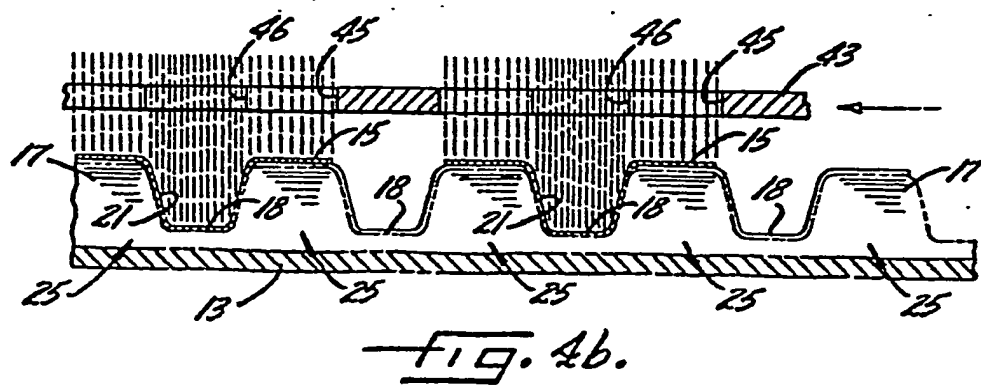
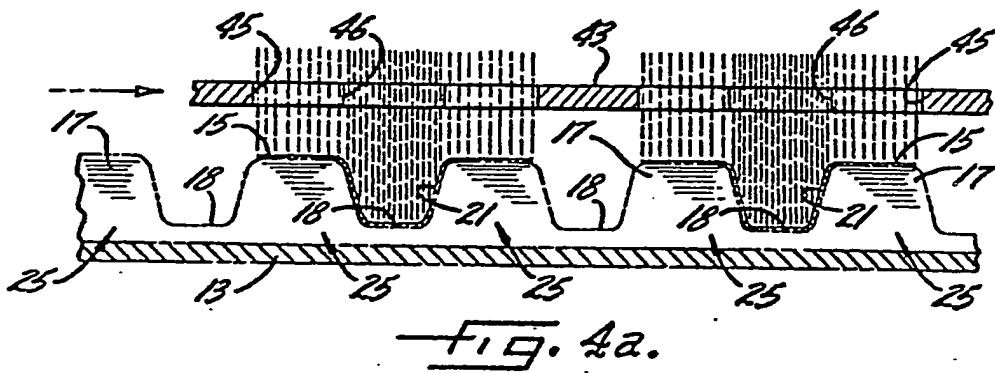
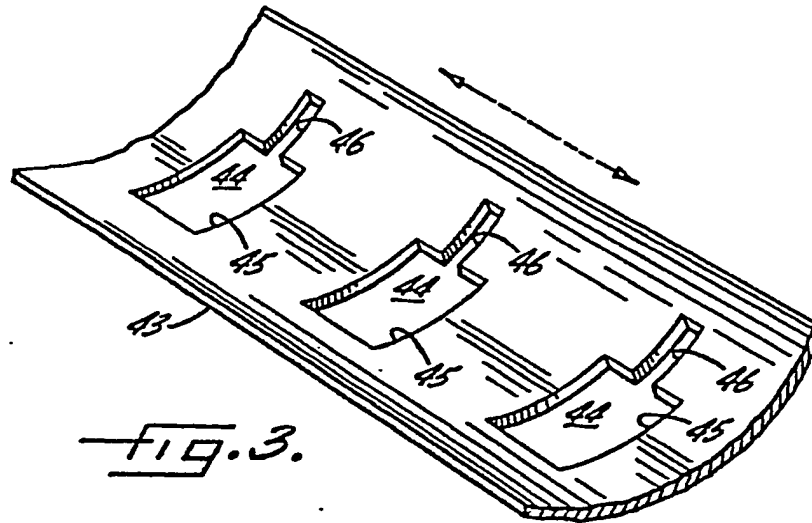
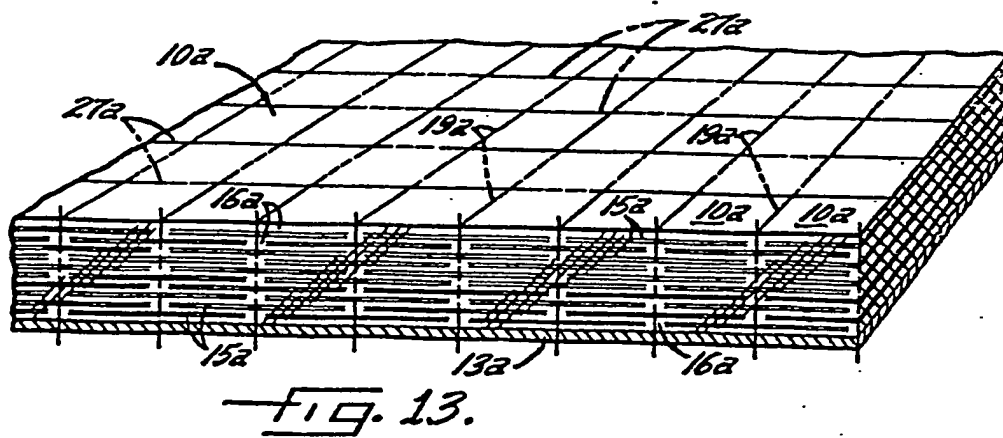
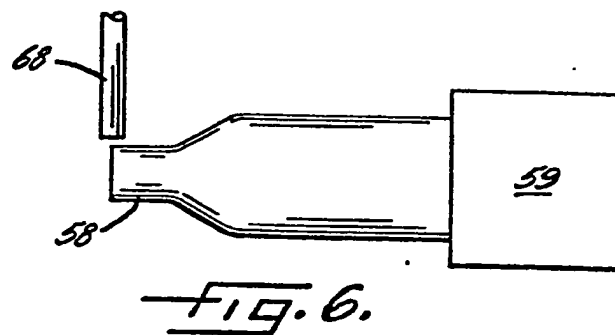
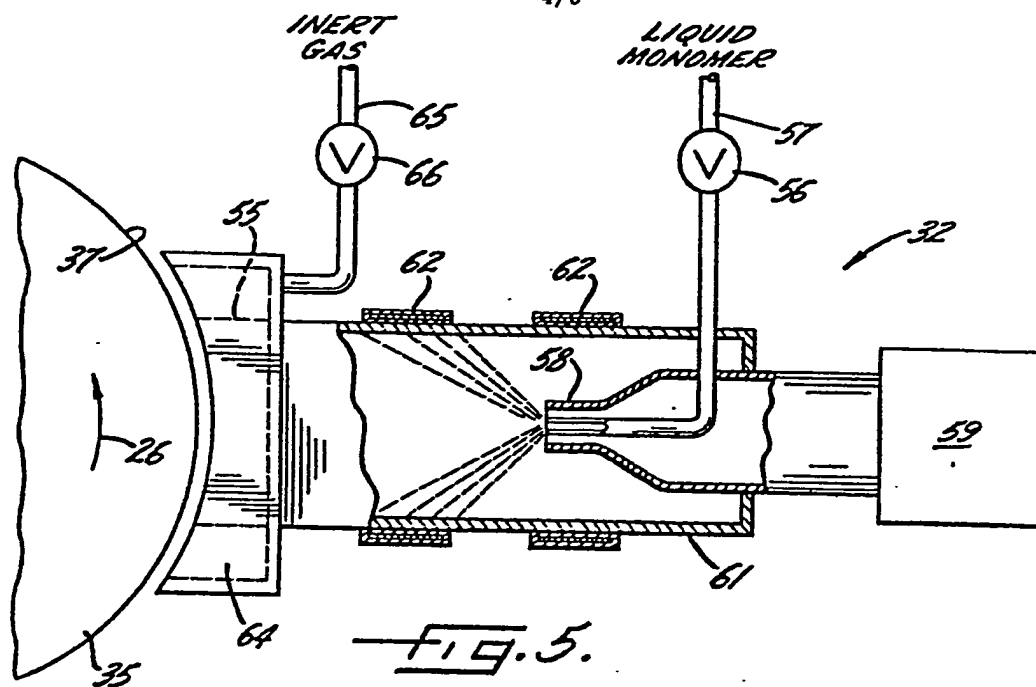


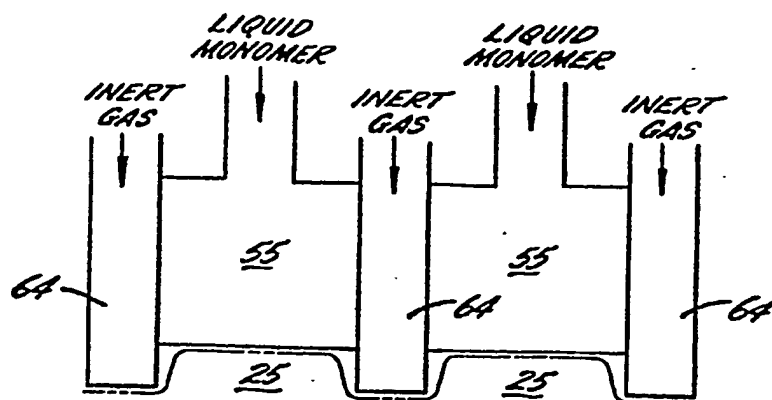
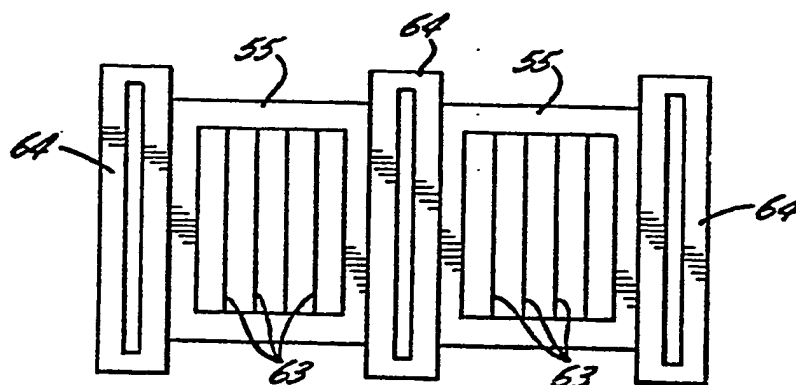
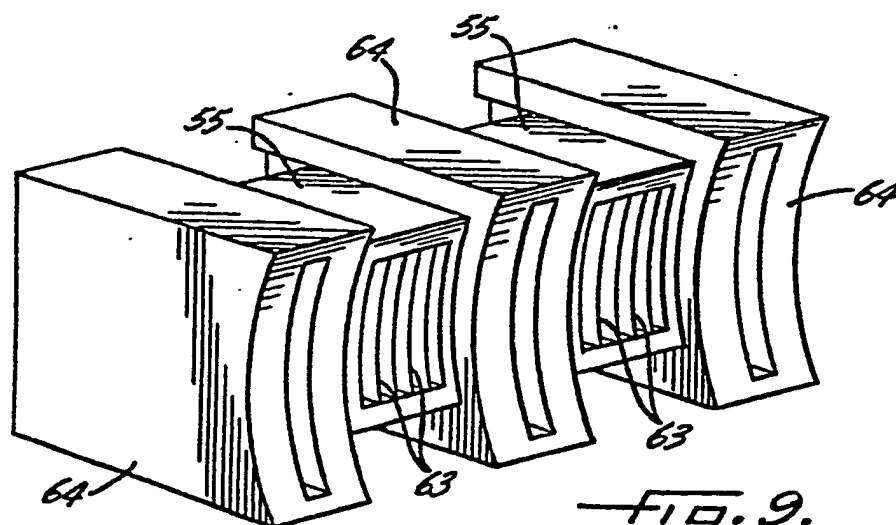
FIG. 10.









FIG. 7.FIG. 8.FIG. 9.

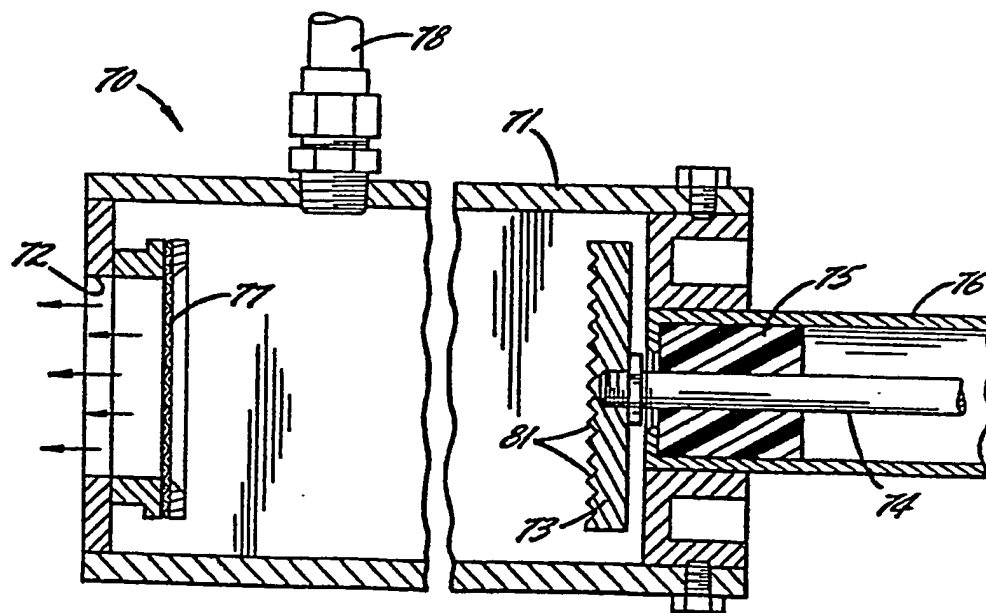
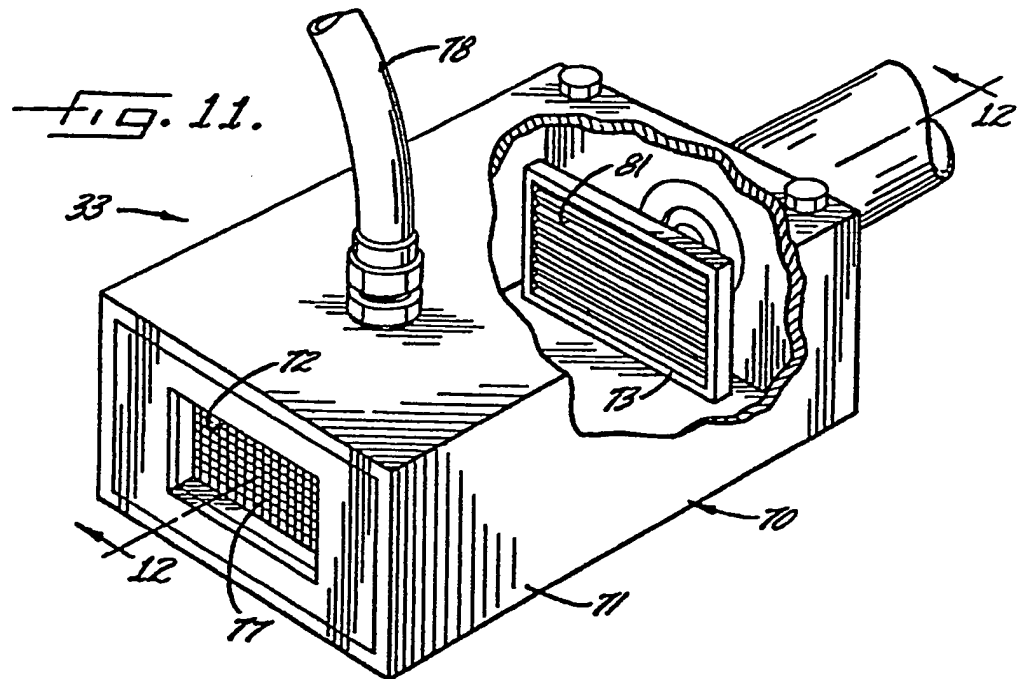


Fig. 12.

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